

Transport properties of quantum dots with hard walls

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(February 6, 2008)

Quantum dots are fabricated in a Ga[Al]As-heterostructure by local oxidation with an atomic force microscope. This technique, in combination with top gate voltages, allows us to generate steep walls at the confining edges and small lateral depletion lengths. The confinement is characterized by low-temperature magnetotransport measurements, from which the dots' energy spectrum is reconstructed. We find that in small dots, the addition spectrum can qualitatively be described within a Fock-Darwin model. For a quantitative analysis, however, a hard-wall confinement has to be considered. In large dots, the energy level spectrum deviates even qualitatively from a Fock-Darwin model. The maximum wall steepness achieved is of the order of 0.4 meV/nm.

I. INTRODUCTION

The electronic transport properties of quantum dots, defined in two-dimensional electron gases in semiconductor heterostructures, have received considerable theoretical as well as experimental attention.¹ In the Coulomb blockade regime, where the quantum dot is only weakly coupled to reservoirs via tunnel barriers, the conductance through the dot shows striking oscillations as a function of a gate voltage which tunes the electrochemical potential inside the dot. The separation between these so-called Coulomb blockade (CB) resonances contains information not only on the single electron charging energy of the dot, but also on its internal energy structure. Within the widely used constant-interaction approximation,^{2,3} the addition spectrum can be decomposed into an electrostatic component given by the total capacitance of the dot, and a chemical component, which reflects the dot's single particle energy spectrum. The Fock-Darwin spectrum^{4,5} has been successfully employed in many experiments to describe the energy level spectrum of quantum dots.^{6–10} These experiments are thus consistent with a harmonic confinement potential in two dimensions; to our knowledge, transport signatures of non-parabolic confinement in quantum dots have not been reported yet. However, it should be emphasized that quantum dots with a hard-wall potential have been fabricated by cleaved-edge overgrowth¹¹ and by self-assembly¹².

The option of patterning quantum dots (and other nanostructures) with hard walls by lithographical means is of interest from both a technological as well as from a physical point of view. One consequence of steep walls is, for example, only a small reduction of the Fermi energy in quantum dots as compared to the bulk value. Electrostatic considerations have established a relation between

the potential steepness and the depletion length.¹³ Thus, steeper confinement is a prerequisite for higher pattern densities. Also, changes in size and shape are reduced as a gate voltage is tuned. This is of particular importance for statistical properties of quantum dots.¹⁴ In addition, recent theoretical results on conductance fluctuations in quantum dots at small magnetic fields are valid only for a hard-wall confinement.¹⁵ We also mention the generalized Kohn theorem,¹⁶ which states that in parabolic potentials, the far infrared conductivity exhibits only a single resonance that corresponds to the characteristic frequency of the bare potential, independent of electron-electron interactions.

In the present paper, we report the fabrication and characterization of quantum dots with super-parabolic confinement potentials. The steepness of the walls is increased by combining local oxidation using an atomic force microscope (AFM) with an additional top gate electrode. Magnetotransport experiments are used to map out the dots' addition spectra, from which the energy levels are reconstructed. The essential idea is to detect a super-parabolic confinement via the dots' energy spectrum in magnetic fields applied perpendicular to the two-dimensional electron gas (Fig. 1): for small Landau level filling factors, a parabolic confinement and a hard-wall confinement generate quite different energy spectra.

We have patterned two quantum dots of different size and fabrication parameters for the present study: for the smaller dot (labelled "dot S"), the spectrum measured is in qualitative agreement with the Fock-Darwin model. However, a quantitative analysis reveals inconsistencies, which dissolve by assuming a hard-wall confinement. For the larger dot (referred to as "dot L"), the energy spectrum differs *qualitatively* from a Fock-Darwin spectrum, and indicates a super-parabolic confinement.

It is well known that in the regime of small filling fac-

tors, a single-particle picture fails to explain the full phenomenology of quantum dots, and charge-density model calculations are used instead.¹⁷ Therefore, we demonstrate that within a charge-density model, our observations can be explained by a steep-wall confinement as well.

The paper is organized as follows: in Section II, the theoretical energy spectra of parabolic dots and hard-wall dots are compared. In Section III, we describe the sample preparation, the experimental setup, and the electronic characterization of two quantum dots. In Section IV, the energy level spectra of the dots are reconstructed from magnetotransport measurements and the results are discussed. In addition, we estimate the steepness of the walls. A summary and conclusion is given in Section V.

II. ENERGY SPECTRA OF PARABOLIC DOTS AND HARD-WALL DOTS

A. The Fock-Darwin model

For a circular dot with a parabolic confinement, characterized by the confining strength ω_0 , the energy spectrum is the well-known Fock-Darwin spectrum^{4,5} (Fig. 1a):

$$E_{N,k} = \hbar(N+k)\sqrt{\omega_0^2 + \frac{1}{4}\omega_C^2} + \frac{1}{2}\hbar(N-k-1)\omega_C \quad (1)$$

Here, we have transformed the radial quantum number m and the angular momentum quantum number ℓ from the standard representation into the Landau level index N ($N=1,2,3,\dots$) and the level index k of the state within a Landau level ($k=0,1,2,\dots$), $k = (m + \frac{|\ell|+\ell}{2})$ and $N = (m + \frac{|\ell|-\ell}{2} + 1)$.¹⁸ Furthermore, ω_C denotes the cyclotron frequency, and each level is assumed to be two-fold spin-degenerate. Throughout the paper, we restrict ourselves to magnetic fields in which only two spin-degenerate Landau levels are occupied, and label the spin-degenerate Landau level N as LL(N), $N = 1,2$. Consequently, the spin-resolved filling factor ν is always in the regime $2 < \nu < 4$.

A corresponding section of the Fock-Darwin spectrum is shown in Fig. 1a. We have chosen typical experimental numbers: a dot radius of $r = 200$ nm, and $\hbar\omega_0 = 1$ meV. As the magnetic field is tuned, the Fermi level varies in zigzag lines, representing the transfer of electrons between the two Landau levels. The energies of LL(1)-states drop as B is increased, while those of LL(2)-states increase. A quasi-periodic level crossing between LL(1)-states and LL(2)-states is obtained. Furthermore, the density of states is identical in both Landau levels. For $\omega_0 < \frac{1}{2}\omega_C$, the separation between adjacent states with identical N can be estimated as $\Delta E_N = E_{N,k+1} - E_{N,k} \approx \hbar\frac{\omega_0^2}{\omega_C}$, and the period in B is approximated to first order by $\Delta B \approx (\frac{\omega_0}{\omega_C})^2 B$, as can

be seen from eq.(1). These approximations are in reasonable agreement with ΔE_N and ΔB in Fig. 1a. Note in particular that ΔB is significantly larger than the “bulk value”, which corresponds to the magnetic field needed to change the number of magnetic flux quanta through the dot area A by one, $\Delta B_{bulk} = \frac{h}{eA} = 33$ mT. Furthermore, the difference in slope between LL(1)-states and LL(2)-states has an upper limit of $\frac{dE_2}{dB} - \frac{dE_1}{dB} = 2\hbar\omega_C/B$.

B. The hard-wall potential

The spectrum of a dot with a hard-wall potential (Fig. 1c) is obtained by numerical calculation of the zeroes of the hypergeometric function ${}_1F_1$, and looks quite different¹⁹: most strikingly, the density of states at the Fermi level in LL(2) is higher than in LL(1), provided the Fermi energy is not far above $\frac{3}{2}\hbar\omega_C$ (Figs. 1c,d). Second, ΔB is well approximated by ΔB_{bulk} . ΔE_N , however, depends sensitively on N , k and the magnetic field.

We note that in the model considerations above, we have neglected spins for clarity. Inclusion of the twofold occupation of each orbital state due to spin is necessary for a quantitative comparison of the models with the experimental data below, and reduces all the above average energy level separations and magnetic field periods by a factor of two.

III. FABRICATION AND CHARACTERIZATION OF THE DOTS

A. Sample fabrication by local oxidation

The samples are patterned out of a shallow Ga[Al]As heterostructure with the two-dimensional electron gas (2DEG) 34 nm below the surface. The quantum dots are defined by local oxidation with an AFM.^{20,21} The height of the oxide lines is roughly equal to the penetration depth of the oxidation into the heterostructure. An oxidation depth of approximately 6 nm depletes the 2DEG underneath. We find that the lateral depletion length ℓ_d can be tailored by the oxidation parameters: ℓ_d increases as the height of the oxide line is increased. The details of this mechanism are still under investigation.²² In a simple picture, however, the oxidation can be understood as a shallow removal of the semiconductor layers, starting at the surface. Removing the oxidized material selectively by a wet etching step does not change the electronic properties of the AFM defined nanostructures. We conclude that the patterned surfaces behave pretty much like a free GaAs (or $\text{Al}_x\text{Ga}_{1-x}\text{As}$, respectively) surface, i.e., the Fermi energy is pinned about mid-gap. Below the oxidized line, the sample surface has moved closer

to the 2DEG, which can lead to a depletion of the mobile electrons. Crucial for the magnitude of the lateral depletion length is the depth of the oxidation process. In shallow 2DEGs it is well known that most of the electrons originating from the Si donors charge surface states, while only a small fraction of them (typically 10 %) go to the heterointerface and lead to the mobile carriers. The oxidized sample surface requires additional electrons per area. If the donor layer remains intact after the oxidation process, these additional electrons are taken from the underlying 2DEG, which is consequently depleted. The lateral depletion length is therefore roughly determined by the distance between the donor layer and the 2DEG. If, however, the oxidation process penetrates down to the donors (a Si δ -layer located 16 nm below the surface), they become electronically inactive in this area, and charges from the neighboring, still intact Si-donors have to compensate the surface potential in the oxidized regions. Consequently, these electrons are now missing for the population of the 2DEG in the vicinity of the oxide lines, and an increased depletion length results. We estimate that ℓ_d is now roughly given by the distance between the 2DEG and the unpatterned sample surface. This line of thought is sketched in Figs. 2c, d. Furthermore, the depletion process is supported by the generation of additional surface states at the edges of the oxidized trenches.

Dot S is defined by oxide lines with an average height of roughly 20 nm and a width of 100 nm. Its lithographic size is 280 nm $\times$ 280 nm (Fig. 2a). The oxide penetrates about 20 nm into the heterostructure and most likely reaches the donor layer. Dot L has a lithographic area of 400 nm $\times$ 420 nm. Here, the oxide lines are kept as shallow as possible (height 10 nm).

After the local oxidation, the samples are covered with a homogeneous top gate (tg) electrode. In Figs. 2c and d, schematic cross sections through the dots are shown.

B. Experimental setup and electronic characterization

The measurements were carried out in the mixing chamber of a $^3\text{He}/^4\text{He}$ -dilution refrigerator with a base temperature of 90 mK. The electron density of the ungated two-dimensional electron gas (2DEG) was $5.5 \cdot 10^{15} \text{m}^{-2}$, and its mobility was 90 m 2 /Vs. DC bias voltages of 20 μV were applied across the dot from source to drain, and the current was measured with a resolution of 500 fA. The measurements were performed in the weak coupling regime, where the quantum point contacts are adjusted to the tunneling regime by voltages applied to the qpc gates in Figs. 2a,b. The conductance is measured as a function of V_I , the gate voltage applied to gate I, and Coulomb blockade (CB) oscillations are observed (Figs. 2e,f). Fits of single CB resonances to the lineshape expected for coherent single-level transport,²

i.e., $G \propto [4k_B T \cosh^2(\frac{E-E_r}{2k_B T})]^{-1}$, reveal an electron temperature of $T_e = 140$ mK (E_r denotes the resonance frequency). Magnetic fields up to $B = 12$ T could be applied perpendicular to the 2DEG.

From measurements of the CB diamonds,¹ we determine the single electron charging energies of $E_C^S = e^2/C_\Sigma^S = 1.22$ meV for dot S, and $E_C^L = 180$ μeV for dot L. By measuring the Coulomb blockade period as a function of the top gate voltage and using the parallel plate capacitor expression, dot S can be modelled as a circular disc with a radius of $r \approx 90$ nm, which corresponds to $\ell_d \approx 50$ nm at $V_{tg} = +100$ mV, the working point for this device. The average single-particle energy level spacing can thus be estimated to $\Delta_S = 140$ μeV . The bulk electron density for this top gate voltage was $n_{2DEG} = 5.9 \cdot 10^{15} \text{m}^{-2}$. At $B = 8.8$ T, the second Landau level is depleted inside the dot, which manifests itself in a sudden transition of the phase diagram structure (not shown)¹⁷. Thus, the electron density inside the dot is reduced by $\approx 20\%$, compared to the two-dimensional value.

For dot L, the single electron charging energy is $E_C^L = 180$ μeV , and from the capacitance between the top gate and the dot, we deduce an electronic dot area of ≈ 400 nm $\cdot$ 400 nm. The shallow oxidation, in combination with a large positive top gate voltage of +390 mV (such that the second two-dimensional subband is still empty) generates extremely small depletion lengths of $\ell_d \approx 15$ nm²¹ and is expected to maximize the steepness of the walls (Fig. 2d) as well. Correspondingly, the single-particle energy level spacing is $\Delta_S \approx 22$ μeV . At $V_{tg} = +390$ mV, we measure $n_{2DEG} = 6.3 \cdot 10^{15} \text{m}^{-2}$. At $B = 11$ T, LL(2) becomes depleted inside the dot, which means that its electron density is only slightly smaller than n_{2DEG} . The parameters of the two dots are summarized in Table I.

It is well established that in quantum dots in the regime of filling factors $2 \leq \nu \leq 4$, the conductance as a function of B and a gate voltage shows periodic patterns over wide ranges of magnetic fields and gate voltages. Furthermore, it has been demonstrated that the energy level spectrum of the dot can be reconstructed from such measurements, which yields information on the confining potential.¹⁷ We therefore characterize our dots by magnetotransport experiments in this regime of filling factors.

Figs. 2e,f compare the corresponding measurements for dot S and L. The small dot (Fig. 2e) shows structures similar to those reported in earlier experiments:^{6,17} as the magnetic field is changed, the CB resonances move in zigzag lines. Their average separation in gate voltage corresponds to one Coulomb blockade oscillation period. Here, the lever arm $\eta = \frac{dE}{dV_I}$ is ≈ 0.11 eV/V, and changes with V_I . We have determined η from measurements of the Coulomb blockade diamonds at $B = 0$.³ In regions where the levels move downwards in energy, their amplitude is high, while in regions where they move upwards in energy, their amplitude is strongly suppressed. Re-

gions of high conductance occur when a state belonging to LL(1) aligns with the Fermi level in source and drain. As the magnetic field increases, their energy is reduced. On the other hand, states belonging to LL(2) will move upwards in energy as B is increased, leading to their depopulation. Since the LL(2) states are residing in the inner region of the dot (Fig. 1b), their coupling to the leads is small, which results in a strongly suppressed peak amplitude.

A similar measurement for dot L, Fig. 2f, reveals a different structure. The CB period at $B = 0$ in this sample is $\Delta V_I = 4.2$ mV. For dot L, we found $\eta = 0.043$ eV/V. In contrast to dot S, the separation between successive stripes of high conductance in V_I - direction does *not* correspond to one CB period at $B=0$, but rather to 2.5 CB periods on average. It is not straightforward to see how the conductive LL(1) states are connected by LL(2) states, i.e., how the zigzag lines run. We will discuss this point in detail in the next Section. Furthermore, there is an overlap between adjacent regions of high conductance along the V_I - direction, which we attribute to thermal activation, since in dot L, the level separation is comparable to $k_B T$ (see Table I).

We emphasize that the structures observed in dots S and L are characteristic for the whole region of $2 \leq \nu \leq 4$, and change only slightly as B is varied.

IV. RECONSTRUCTION OF THE ENERGY SPECTRA

In this Section, we construct the energy level spectra of the two dots from the measurements of Figs. 2e and f. While this is straightforward for dot S, it requires a more detailed understanding of the addition spectrum measured for dot L, which we gather from activated transport experiments. The spectra obtained will be compared to the model potentials described in Section II, with the spin splitting included.

A. Energy spectrum of dot S

In Fig. 3a, the occupation numbers of LL(1) and LL(2) and the corresponding “phase diagram” are compared to the measurement. Here, a phase is given by (n_1, n_2) , where n_i denotes the number of electrons in LL(i). The gaps between the zigzag lines in energy (gate voltage) direction correspond to the charging energy e^2/C_Σ , plus the separation between the single-particle energy levels inside the dot. From Fig. 3a, we use the lever arm η (see Table I) to subtract E_C^S , and obtain bright lines, Fig. 3b, which correspond to the magnetic field dependence of adjacent LL(1) states. The slightly alternating separations reflect the Zeemann splitting. An average spacing

between neighboring LL(i) - states of $\Delta_1^S = 310$ μ eV, and $\Delta_2^S \approx 400$ μ eV is extracted. Note that since the LL(2) states are not directly visible, their position can only be guessed from the point where the bright lines corresponding to the LL(1) states overlap, and Δ_2^S can be no more than a rough estimate.

The Fock-Darwin model in the limit of strong magnetic fields states that $\Delta_1^S = \Delta_2^S \approx \frac{\hbar}{2} \frac{\omega_C^2}{\omega_C}$ (the factor of $\frac{1}{2}$ takes the spin splitting into account), from which we obtain $\hbar\omega_0 \approx 2.75$ meV, an at first sight reasonable, although large value. Further analysis, however, reveals problems with the interpretation in terms of a Fock-Darwin model: (i) Since $r = 90$ nm, we can calculate E_F inside the dot from $E_F = \frac{1}{2} m^* \omega_0^2 r^2$, which would result in $E_F = 27$ meV, *larger* than in the 2DEG.

(ii) We observe $\Delta B = 75$ mT. Within the Fock-Darwin model in strong magnetic fields, however, $\Delta B \approx \frac{1}{2} (\frac{\omega_0}{\omega_C})^2 B \approx 180$ mT, is expected.

(iii) The slope of the energy levels, $\frac{dE_i}{dB}$ (i denotes the LL index) deviates from the Fock-Darwin values: here, $\frac{dE_2}{dB} - \frac{dE_1}{dB} \approx 2\hbar\omega_C/B$, as observed experimentally in previous work.⁶ However, we estimate $\frac{dE_2}{dB} - \frac{dE_1}{dB} \approx 5\hbar\omega_C/B$, which is much too large, even considering the experimental uncertainty in $\frac{dE_2}{dB}$.

These inconsistencies can be significantly reduced by assuming a hard-wall potential. We measure $\frac{1}{2} \Delta B_{bulk} \approx 80$ mT, in reasonable agreement with the ΔB_{bulk} expected for $r = 90$ nm. Also, both the energy level separation and $\frac{dE_2}{dB} - \frac{dE_1}{dB}$ can be much larger than in a parabolic dot.

Hence, although the behavior of dot S is in qualitative agreement with a parabolic confinement, a quantitative analysis suggests that its confinement resembles a hard-wall potential.

B. Energy spectrum of dot L

The period in V_I of the conductive regions in dot L does not correspond to the Coulomb blockade oscillation period at $B=0$, as it does in dot S. In order to obtain more information on the states with suppressed conductance, we measured the Coulomb diamonds, i.e. the conductance as a function of both V_I and the source-drain voltage V_{sd} , at $B = 8$ T (Fig. 4). At *large* bias voltages, i.e. for $|V_{sd}| > 200$ μ V, an average CB oscillation period of $\Delta V_I = e/C_I = 3.5$ mV is observed, slightly smaller than ΔV_I observed at $B=0$. As $|V_{sd}|$ is reduced, the conductance gets suppressed for 70 % of the CB resonances, corresponding to a ratio between suppressed peaks and visible peaks of 2.5:1. The conductance doublets in V_g -direction, Fig. 2f, remain visible at small $|V_{sd}|$. Furthermore, the shape of the diamonds with suppressed conductance tends to follow the shape of the nearest diamond in which the conductance outside the Coulomb blockade is not suppressed, which indicates that the activated current flows predominantly via LL(1)

states. These observations lead us to conclude that the density of LL(2) states at the Fermi level is about 2.5 times the density of LL(1) states. LL(2) states get occupied when aligned with the Fermi energy, but since their coupling to the leads is negligible, transport via these states is not measurable, even at large V_{sd} . Rather, transport occurs via excitation of LL(1) states.

With this information, we are now able to reconstruct the energy level spectrum of dot L by subtracting the E_C from the addition spectrum of Fig. 2f. The phase diagram is shown in Fig. 3c. Here, we have determined the phase boundaries due to LL(2) states from the activated transport measurements of Fig. 4, concluding that we must cross ≈ 2.5 LL(2)-states on average between adjacent LL(1)-states. The zigzag lines obtained are again separated by one Coulomb period in V_I , and it can be seen that the different structure originates in the fact that most states at the Fermi level couple extremely poorly to the leads. We point out that alternative choices of the phase boundaries are inconsistent not only with the activated transport measurements, but also with other considerations: if we were to assume that the LL(2) states run like the white, dashed line connecting point 1 and 2 in Fig. 3c, we would cross 3.5 LL(2) states on average between adjacent LL(1) states. In addition, all energy levels would run downwards in energy as B is increased, which would lead to an unphysical population of the dot with electrons by increasing B. If we, on the other hand, were to assume that the LL(2) states run parallel to the line between point 1 and 3, we would cross equally many LL(2) states as LL(1) states as V_I is tuned, in clear contradiction to the activated transport experiments. Also, the slope of the LL(2) states would be 25 meV/T, which is approximately one order of magnitude larger than their maximum slope of $\frac{3}{2}\hbar\omega_C/B$, and we would obtain an unphysically small period for the “Magneto-Coulomb blockade oscillations”,²³ which means that a change in magnetic field of only 10 mT would be sufficient to change the total number of electrons in the dot by one.

Performing the same procedure as before, we reconstruct the energy spectrum of dot L, Fig. 3d. An energy level separation between LL(1) states of $\Delta_1^L = 160 \mu\text{eV}$, and $\Delta_2^L = 60 \mu\text{eV}$ for LL(2) is found. Hence, the density of LL(2) states at the Fermi level is 2.5 times greater than the density of LL(1) states, which indicates a significant deviation from a Fock-Darwin potential. In addition, note that $\Delta B = 13 \text{ mT} = \frac{1}{2}\Delta B_{\text{bulk}}$. This is expected for a hard-wall dot, since for each additional flux quantum, two LL(1) states are generated.

We thus conclude that the energy spectrum of dot L deviates even qualitatively from the Fock-Darwin model, but agrees well with a hard-wall confinement. In Table I, we compare the parameters of the two dots.

C. Hard walls and the charge density model

So far, we have discussed the energy level spectra within a single-particle picture, and found strong evidence for super-parabolic confinement. It is, however, well-known that certain aspects of the energy spectrum of quantum dots cannot be understood in such a simple picture, but are rather interpreted in terms of a charge-density model.²⁴ This is particularly true when strong magnetic fields are present,^{17,23,25} and therefore raises the question whether our observations hint towards steep walls also within a charge-density model. To answer this issue, we study the depletion of dot L along the vertical arrow in Fig. 3c, i.e., as we proceed from point A to point E. For comparison, we first look at the depletion process within the single-particle picture. The corresponding changes in the energies E_i of LL(i) are depicted in Fig. 5a. At our starting point A, we have removed an electron from LL(1) into the reservoirs. At point B, a LL(2)-electron is transferred into the leads. This, however, does not lead to significant conductance, since the coupling of the LL(2)-states to the leads is poor. In point B, the energy of LL(2) drops by $\Delta_2^L + E_C$, and that one of LL(1) by just E_C . The same process takes place at points C and D, with the corresponding energy shifts. At point E, the next LL(1)-electron is removed from the dot. Consequently, 3 electrons have been removed from LL(2) and one from LL(1). In order to repeat this process cyclically, Δ_1^L has to be larger than Δ_2^L . This is what we have already established above. At increased source-drain bias voltages, we would start to see activated transport via nearby LL(1)-states at some points between A and E. The magnitude of V_I at such activated processes is given by the points where the black, dashed lines intersect with the arrow. The separation between the phase boundary and the arrow is a measure of the activation energy necessary. These varying activation energies give rise to the observed “meta-diamonds” in Fig. 4.

Within a charge-density model, the measured phase diagram gets a different interpretation:^{17,24,26} For filling factors $2 \leq \nu \leq 4$, LL(1) forms a compressible ring at the dot edge, Fig. 5b. At the Fermi level, LL(2) is spatially separated from this ring by an incompressible region and forms a compressible disk in the dot center; n_i in Fig. 3c now denotes the number of electrons in the outer ring ($i=1$) and in the center disc ($i=2$). Here, we assume that spin splitting does not generate an additional electrostatic structure. The two compressible regions are coupled via an intra-dot capacitance C_{12} ; charging the outer ring will now change the electrostatic energy of the inner dot by $E_{12} = e^2/C_{12}$. If we perform a gate sweep similar to the one indicated by the arrow in Fig. 3b, a removal of an electron from the outer ring would change the energy of the ring by $E_{C,1}$, and the one of the inner dot by E_{12} .²³ Similarly, removing an electron from the inner dot changes its energy by $E_{C,2}$, and that one of the ring by E_{12} , which gives rise to the energy

ladder depicted in Fig. 5c. Within this picture, $E_{C,i}$, $i=1,2$ reflect the single electron charging energies of the two compressible regions, and hence the size, of the outer ring and the inner dot, respectively. Since $E_{C,1} > E_{C,2}$, the area of the ring must be smaller than the area of the inner dot. This means that the width of the outer compressible stripe, w_1 , is small compared to the dot radius. In previous work, the relation between the width of the compressible regions and the potential profile has been well established:²⁴ $w_1 \propto (dn(x)/dx)^{-1}$, where $n(x)$ is the local electron density and x the distance from the edge of the dot. Since $dn(x)/dx$ is proportional to the electric field at x , we conclude that also within the charge-density model, the potential walls are steep.

D. Estimation of the wall steepness

While we observe clear signatures of super-parabolic confinement, it is not straightforward to determine the actual steepness of the walls. We can give no more than an order of magnitude estimate for the edge steepness $\frac{dE}{dx}$. According to Sivan and Imry²⁷, one can approximate Δ_1 in a hard-wall dot by $\Delta_1 \approx \hbar\omega_C\ell_B/L$, where ℓ_B denotes the magnetic length and L the dot diameter. Our measurements of Δ_1 are in good agreement with this expression, which indicates that the level separation is not strongly reduced by a finite wall steepness. We can estimate the steepness at the Fermi level in dot S from the Fock-Darwin model, despite its shortcomings, to $\frac{dE}{dx} = m^*\omega_0^2r$, which gives $\frac{dE}{dx} \approx 0.6$ meV/nm. Furthermore, the charge-density model can be quantified in some more detail for dot L. Since E_{12} corresponds to the separation between adjacent conductive regions in Fig. 3c, we estimate $C_{12} \approx 60aF$. We denote the width of the outermost compressible stripe by w_1 , and the width of the incompressible stripe as a_1 (see Fig. 5b). The ratio between the area of center region and the outer ring is about 2.5, since we have 2.5 times more levels in the inner region than in the outer ring. We use the formula for a planar capacitor²⁶ to estimate the ratio $\frac{w_1}{a_1} \approx \frac{1}{4}\exp(C_{12}/4\epsilon\epsilon_0r) \approx 0.5$, leading to $w_1 \approx 25$ nm and $a_1 \approx 50$ nm. The Fermi energy drops completely over the distance a_1 . Hence, we can estimate $[\frac{dE}{dx}]_L \approx \frac{E_F}{a_1} \approx 400$ μ eV/nm. This is the *average* wall steepness. The edge of dot L is thus about one order of magnitude steeper than in conventional dots, as estimated from self-consistent charge-density functional calculations.¹⁷ Since the lateral depletion length is smaller in dot L than in dot S, one might qualitatively expect that the wall steepness is larger. This, however, is not clearly supported by our data.

V. SUMMARY

In conclusion, we have demonstrated that by local oxidation of semiconductor heterostructures with an atomic force microscope, nanostructures with steep walls can be fabricated. Empirically, the height of the oxidized lines determines the lateral depletion length. Using quantum dots as an example, we have shown via magnetotransport experiments that the confinement can be super-parabolic, i.e., it resembles more a hard-wall potential than a parabolic potential. The deviations from a parabolic confinement become more pronounced as the dot size is increased. The average wall steepness is of the order of 0.4 meV/nm.

We would like to thank T. Ihn an enlightening discussion. Financial support by the Swiss National Science Foundation is gratefully acknowledged.

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- ¹ For a review, see L.P. Kouwenhoven, C.M. Marcus, P.L. McEuen, S. Tarucha, R.M. Westervelt, and N.S. Wingreen, in *Mesoscopic Electron Transport*, Proceedings of a NATO Advanced Study Institute, edited by L.P. Kouwenhoven, G. Schön and L. L. Sohn, (Kluwer, Dordrecht, Netherlands, 1997), ser. E, vol. 345, pp. 105-214.
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TABLE I.

Characteristics of the two dots. Δ denotes the average, spin-resolved level spacing, as estimated from the dot size, while Δ_i is the level spacing in Landau level i , as obtained from the reconstruction of the energy spectra. Furthermore, $\eta = \frac{dE}{dV_I}$ denotes the lever arm.

Dot	Small dot (S)	Large dot (L)
n_{2DEG}	$5.9 \cdot 10^{-15} \text{ m}^{-2}$	$6.3 \cdot 10^{-15} \text{ m}^{-2}$
lithographic size	280 nm $\times$ 280 nm	400 nm $\times$ 420 nm
$E_C = e^2/C_\Sigma$	1.22 meV	0.18 meV
electronic dot size	radius: 90 nm	$\approx$ 400 nm $\times$ 400 nm
Δ	140 μeV	22 μeV
η	0.11 eV/V	0.043 eV/V
Δ_1	310 μeV	160 μeV
Δ_2	400 μeV	60 μeV

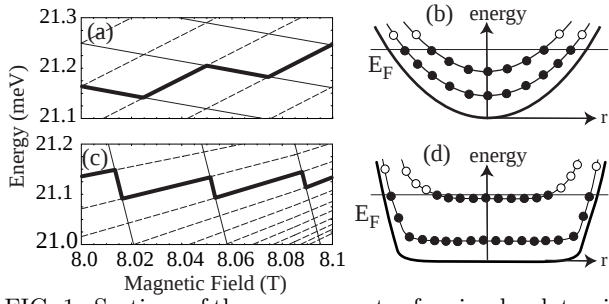


FIG. 1. Sections of the energy spectra for circular dots with a radius of 200 nm and a filling factor $2 < \nu < 4$, with a parabolic confinement, $\hbar\omega_0 = 1$ meV (a) and a hard-wall confinement (c). States belonging to LL(1) (thin full lines) reduce their energy as B is increased, while those belonging to LL(2) (dashed lines) are running upwards in energy. The bold lines represent the Fermi level when the number of electrons in the dot is constant. In a parabolic dot, the density of states in LL(1) and LL(2) are identical (a,b), while in a hard-wall dot (c,d), the density of states in LL(2) is much larger than in LL(1) at the Fermi level. In (b) and (d), the full circles indicate occupied energy levels, while open circles represent empty states.

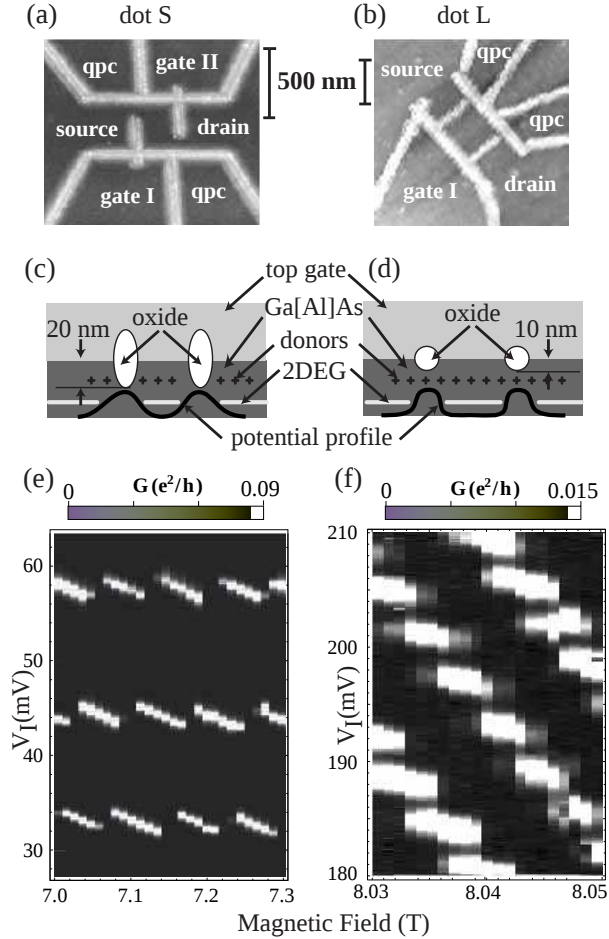


FIG. 2. Surface topography of the two dots (the small dot S, (a), and the large dot L (b)) under study, taken with an AFM before the evaporation of the homogeneous top gate electrode. The bright lines are oxide lines, below which the electron gas is depleted (see text). Both dots are tuned by a voltage applied to planar gate I. The gates labelled “qpc” are used to adjust the coupling to source and drain. Dot S has a lithographic size of $280 \text{ nm} \times 280 \text{ nm}$, while the oxide lines are $\approx 20 \text{ nm}$ in height and 80 nm in width. Dot L is $420 \text{ nm} \times 400 \text{ nm}$ in lithographic area. Here, the oxide lines are shallower (height 10 nm) and broader (120 nm). Schematic cross sections through dot S and dot L are shown in (c) and (d), respectively, including the top gate. Sketched are also the oxide lines (white ovals) and the resulting potential profile. The 2DEG is 34 nm below the surface. The conductance G of dots S and L at $2 \leq \nu \leq 4$ as a function of magnetic field and V_I are shown in (e) and (f), respectively, in a gray scale plot. The data are taken at a temperature of 90 mK. Both dots show a large conductance (bright areas) only if a LL(1)-state aligns with the Fermi level in the leads (see text).

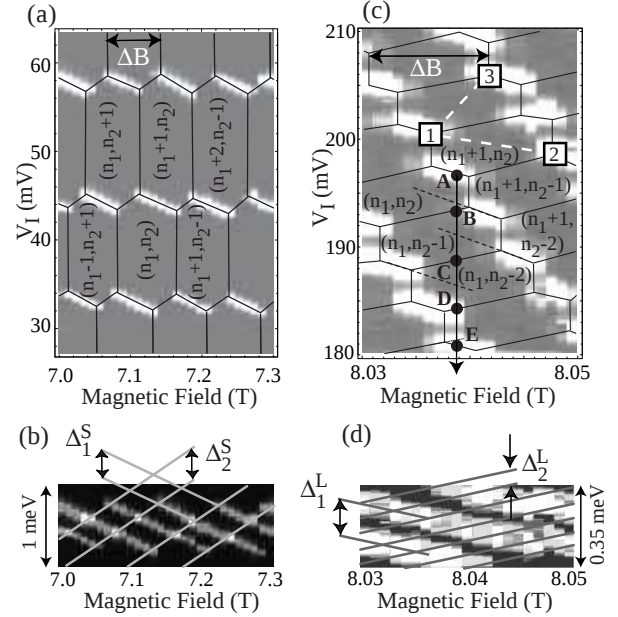


FIG. 3. (a) Sketched phase diagram of the small dot, as an overlay on the data of Fig.1(a). Each phase is given by (n_1, n_2) , where n_i denotes the number of electrons in LL(i). If n_2 changes, the conductance remains zero, due to the poor coupling to the leads. A change in n_1 results in a high conductance. (b): reconstruction of the energy level spectrum. We find the level spacings $\Delta_1^S = 310 \mu\text{eV}$, $\Delta_2^S \approx 400 \mu\text{eV}$. (c) Phase diagram of the large dot, as an overlay on the data of Fig.1(b). The phases have the same meaning as in (a). See text on how they were determined. The dark, dashed lines indicate excited LL(1) states. As the capital letters and the bold circles, they refer to Fig. 5 (see text). The bright, dashed lines and the numbers in the white squares denote alternative, but unphysical phase boundaries, and are discussed in the text as well. (d): Reconstruction of the energy level spectrum. The level spacings $\Delta_1^L = 160 \mu\text{eV}$, and $\Delta_2^L \approx 60 \mu\text{eV}$ are found.

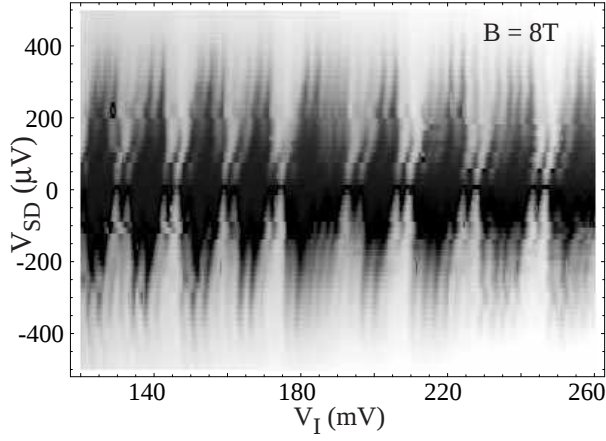


FIG. 4. Coulomb diamonds of the large dot, measured over 40 Coulomb blockade periods, in a gray scale plot. For each completely visible Coulomb diamond, between 2 and 4 diamonds are suppressed, in which the Coulomb blockade oscillations can be observed only under sufficiently large source-drain bias voltages ($|V_{sd}| > 200\mu V$). The resulting “meta-diamonds” correspond to the energy necessary to carry current via excited LL(1) - states, see text.

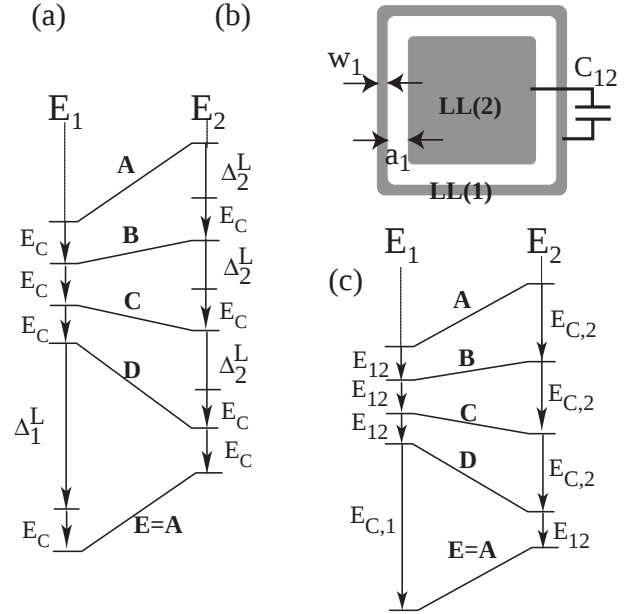


FIG. 5. Energies E_1 and E_2 of LL(1) and LL(2) as the large dot is depleted along the arrow in Fig.3(c), in the single- particle picture (a). Within the charge density model, the dot develops an internal electrostatic structure (b). A compressible ring of LL(1) states at the Fermi level is separated by an incompressible region (white) from the compressible region formed by LL(2) states in the center of the dot, and an additional capacitance forms inside the dot. Here, w_1 and a_1 denote the width of the outer compressible region and of the incompressible region, respectively. (c): Energies of the core and the ring in the charge density model as the dot is depleted (see text).